

ABSTRACT

At least one high-k device, and a method for forming the at least one high-k device, comprising the following. A structure having a strained substrate formed thereover. The strained substrate comprising at least an uppermost strained-Si epi layer. At least one dielectric gate oxide portion over the strained substrate. The at least one dielectric gate oxide portion having a dielectric constant of greater than about 4.0. A device over each of the at least one dielectric gate oxide portion to complete the least one high-k device. A method of forming the at least one high-k device.